

EAST: [10728514:sonos stepped channel.wsp:1]

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	#	+	Inventor	Document#	Year	P	Title	Current	Current	Current	Retrieval	S	C	P	Image	Doc.	P
1			Ogura, Seiki	US 6886632	2004	2	Dual-bit multi-level ballistic MONOS memory	257/374	257/325			R	F	F	F	F	US 6886632
2			Kim, Seong-G	US 2004015	2004	1	Non-volatile SONOS memory device and met	257/324				R	F	F	F	F	US 2004015
3			Letavic, Tod	US 2003006	2003	1	SELF-ALIGNED DUAL-OXIDE UMOSFET DEVI	257/330	257/324			R	F	F	F	F	US 2003006
4			Vyvoda, Mich	US 6710409	2004	1	Inverted staggered thin film transistor with a	257/347	257/315			R	F	F	F	F	US 6710409
5			Nakao, Hiron	US 5589700	1996	1	Semiconductor nonvolatile memory	257/325	257/410			R	F	F	F	F	US 5589700
6			Hong, Gary	US 5414287	1995	1	Process for high density split-gate memory c	257/316	257/322			R	F	F	F	F	US 5414287
7			Shimoji, Nori	US 5319228	1994	1	Semiconductor nonvolatile memory with wid	257/324	257/406			R	F	F	F	F	US 5319228
8			Iwai, Hiroshi	US 5237188	1993	5	Semiconductor device with nitrided gate ins	257/325	257/411			R	F	F	F	F	US 5237188
9			Rosler, Bern	US 4087795	1978	4	Memory field effect storage device	385/185	257/321			R	F	F	F	F	US 4087795

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